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Patent and Trademark OfficeAttorney Docket No.
740756-2419Serial No. Not Yet
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INFORMATION DISCLOSURE STATEMENT

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10/035441
01/04/02

Applicant: Naoaki YAMAGUCHI et al.

Filing Date: January 4, 2002 Group: 1746

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
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Examiner *Unita Laude*Date Considered *2/10/03*

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INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)							
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FOREIGN PATENT DOCUMENTS							
	Document Number	Date	Country	Class	Subclass	Translation Yes	No
✓	05-243576	09/21/1993	Japan			Abstract	
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
✓	F. Ueno, "Observation of fast microscopic phase change phenomena of chalcogenide thin films", Japanese Journal of Applied Physics, Supplement, Vol. 26, Supplement 26-4, pp. 55-60, 1987.						
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Examiner <i>unita olema</i>				Date Considered <i>2/10/03</i>			
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				Application Number	10/035,441
				Filing Date	January 4, 2002
				First Named Inventor	Naoaki YAMAGUCHI et al.
				Group Art Unit	1746
				Examiner Name	Unassigned
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